

STP60NF06

General features

Туре	V _{DSS}	R _{DS(on)}	۱ _D
STP60NF06	60V	<0.016Ω	60A

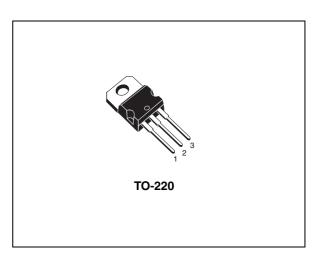
- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Description

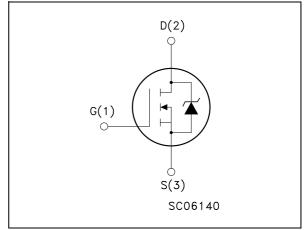
This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced highefficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

Applications

Switching application



Internal schematic diagram



Order code

Part number	Marking	Package	Packaging
STP60NF06	P60NF06	TO-220	Tube

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1 Electrical ratings

Table 1.	Absolute	maximum	ratings
	Abounde	IIIuAIIIIuIII	ruungo

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage (V _{GS} = 0)	60	V
V _{GS}	Gate- source voltage	±20	V
I _D	Drain current (continuos) at $T_C = 25^{\circ}C$	60	Α
Ι _D	Drain current (continuos) at T _C = 100°C	42	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	240	Α
P _{TOT}	Total dissipation at $T_{C} = 25^{\circ}C$	110	W
	Derating factor	0.74	W/°C
dv/dt ⁽²⁾	Peak diode recovery voltage slope	7.5	V/ns
T _{stg}	Storage temperature	– 55 to 175	°C
Тj	Max. operating junction temperature	- 55 10 175	U

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 60A$, di/dt $\leq 400 A/\mu s$, $V_{DD} \leq 48V$, $Tj \leq T_{jmax}$

Table 2.Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	1.36	°C/W
R _{thj-a}	Thermal resistance junction-ambient max	62.5	°C/W
Т	Maximum lead temperature for soldering purpose	300	°C

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	30	А
E _{AS}	Single pulse avalanche energy (starting Tj=25°C, Id=Iar, Vdd=30V)	370	mJ

2 Electrical characteristics

(T_{CASE} =25°C unless otherwise specified)

	On/on states					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown voltage	I _D = 250 μA, V _{GS} = 0	60			V
	Zero gate voltage	V _{DS} = Max rating			1	μA
IDSS	Drain current (V _{GS} = 0)	V_{DS} =Max rating, T _C =125°C			10	μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	$V_{GS} = \pm 20V$			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2		4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 30A		0.014	0.016	Ω

Table 4. On/off states

Table 5. Dynamic

	Bynanne					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} = 15V _, I _D =30A		50		S
C _{iss}	Input capacitance			1660		pF
C _{oss}	Output capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		400		pF
C _{rss}	Reverse transfer capacitance	$V_{GS} = 0$		140		pF
Qg	Total gate charge	V _{DD} = 30V, I _D = 60A,		54	73	nC
Q _{gs}	Gate-source charge	$V_{\text{DD}} = 30\text{V}, I_{\text{D}} = 60\text{A},$ $V_{\text{GS}} = 10\text{V}$		9		nC
Q _{gd}	Gate-drain charge	(see Figure 12)		23		nC

1. Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r	Turn-on delay time Rise time			15 65		ns ns
t _{d(off)} t _f	Turn-off-delay time Fall time	$V_{DD} = 30V, I_D = 30A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 11)		45 20		ns ns

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I _{SD}	Source-drain current				60	Α
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				240	А
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 60A, V _{GS} = 0			1.3	۷
t _{rr} Q _{rr}	Reverse recovery time Reverse recovery charge	I _{SD} = 60A, V _{DD} =30V di/dt = 100A/µs, Tj = 150°C		70 185		ns nC
I _{RRM}	Reverse recovery current	(see Figure 13)		5		А

Table 7.Source drain diode

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%



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 $Z_{th} = k R_{thJ-c}$

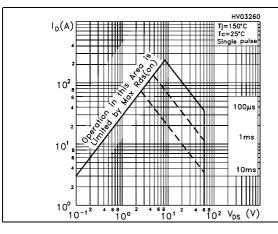
10⁻¹ † p (s)

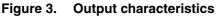
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 $\delta=\,{\rm t_p}\,/\tau$

Electrical characteristics (curves) 2.1

Figure 1. Safe operating area





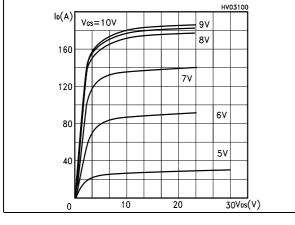
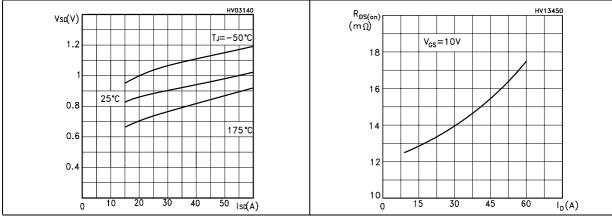


Figure 5. Source-drain diode forward characteristics





Thermal impedance

0.05 0.05

0.01

10⁻³

10⁻²

SINGLE PULSE

Figure 2.

κ

10

10⁻²

 $\delta = 0.5$

0.1

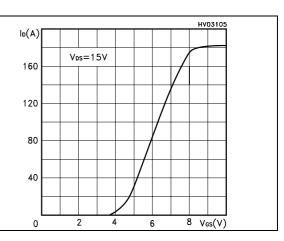
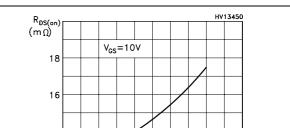
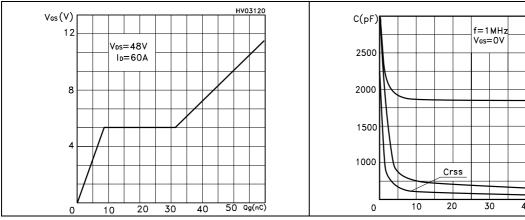


Figure 6. Static drain-source on resistance





Gate charge vs gate-source voltage Figure 8. Capacitance variations Figure 7.

Figure 9. Normalized gate threshold voltage vs temperature

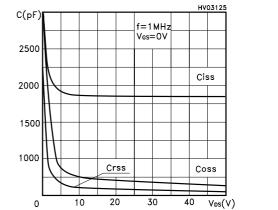
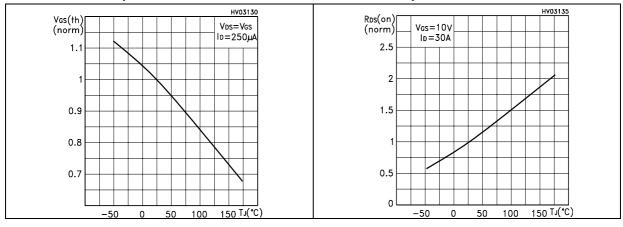
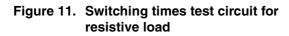


Figure 10. Normalized on resistance vs temperature



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3 Test circuit



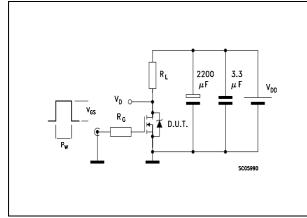
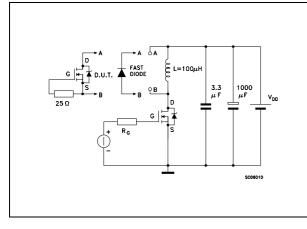
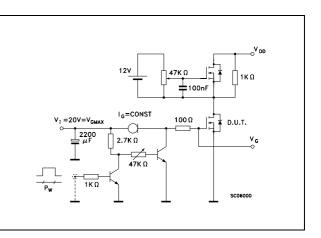


Figure 13. Test circuit for inductive load switching and diode recovery times









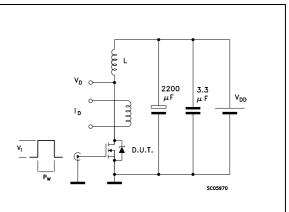
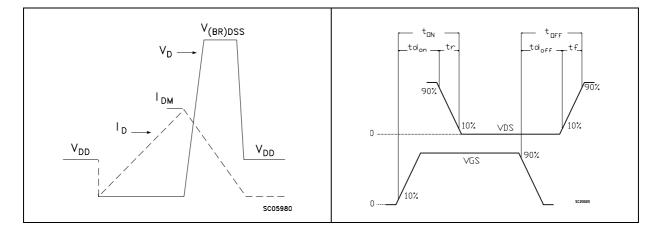


Figure 16. Switching time waveform



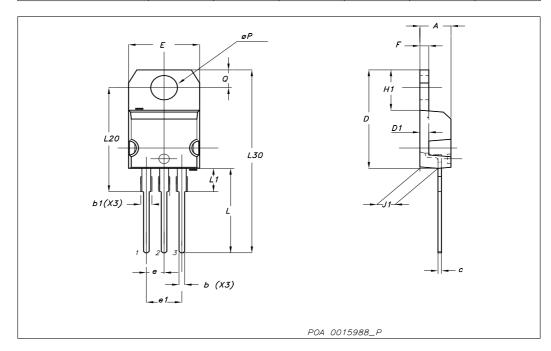
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*



Dim		mm				
Dim	Min	Тур	Мах	Min	Тур	Max
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
θΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

TO-220 mechanical data





5 Revision history

Date	Revision	Changes
09-Sep-2004	3	Complete version
17-Aug-2006	4	The document has been reformatted
04-Oct-2006	5	Changes in <i>Dynamic</i>
02-Mar-2007	6	Safe operating area has been updated



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